

Silicon PNP Power Transistors

2SA1108

DESCRIPTION

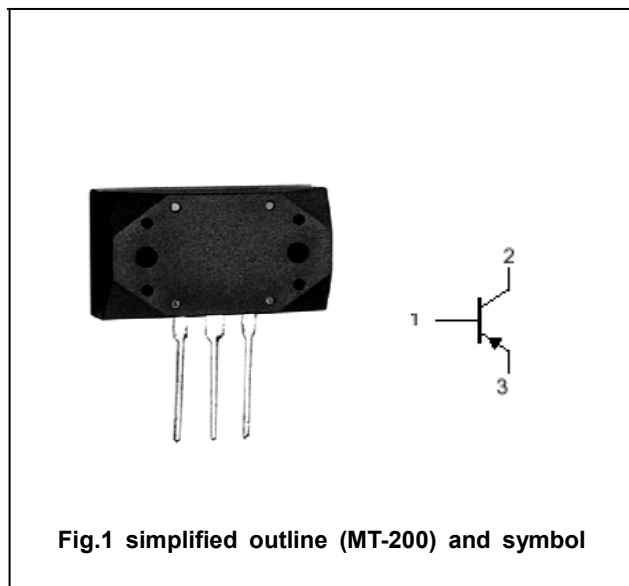
- With MT-200 package
- High power dissipation

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-130	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-1.2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	120	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA$; $I_B=0$	-130			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA$; $I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A$; $I_B=-0.5A$			-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-5A$; $V_{CE}=-5V$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-130V$; $I_E=0$			-5	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-5	μA
h_{FE-1}	DC current gain	$I_C=-2A$; $V_{CE}=-5V$	55		160	
h_{FE-2}	DC current gain	$I_C=-5A$; $V_{CE}=-5V$	35			
f_T	Transition frequency	$I_C=-1A$; $V_{CE}=-10V$		60		MHz

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PACKAGE OUTLINE

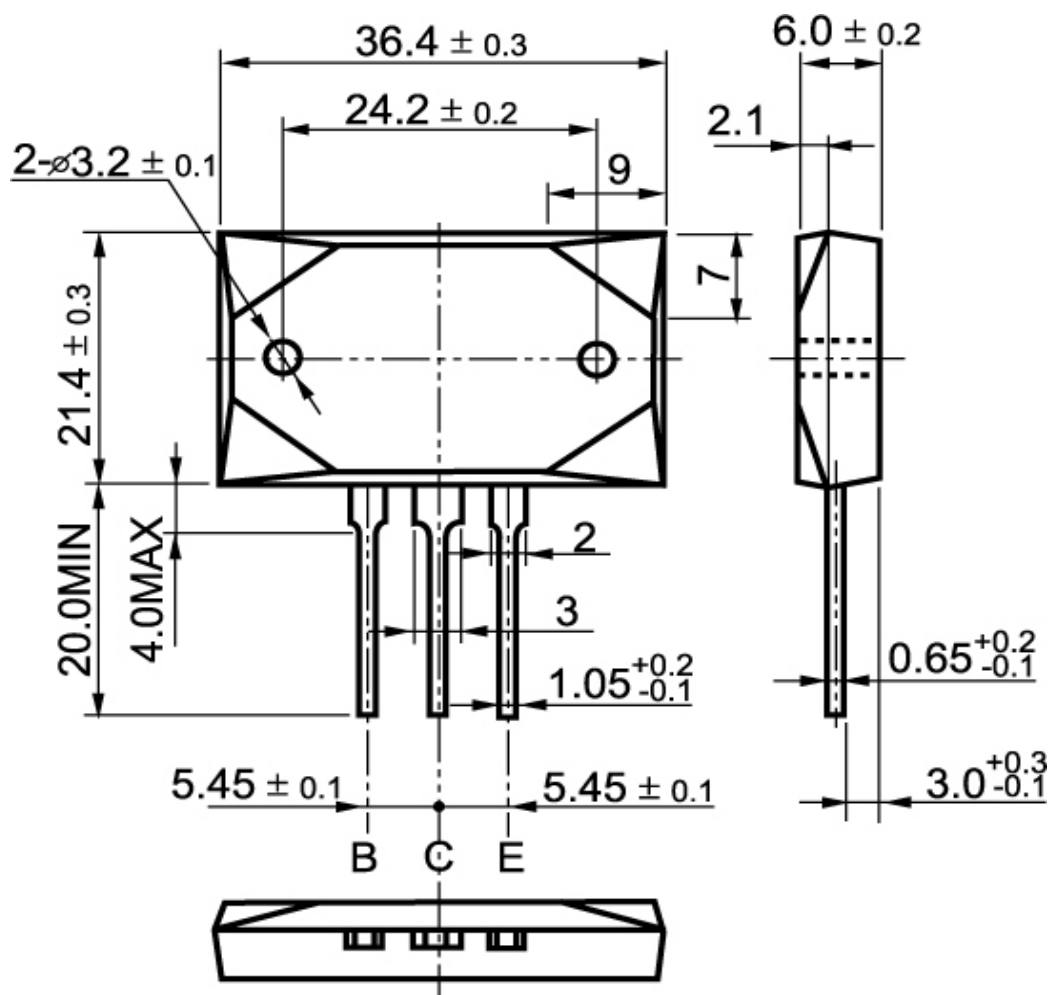


Fig.2 outline dimensions